BLF2425M7L140; BLF2425M7LS140

Power LDMOS transistor

Rev. 1 — 30 January 2012

Objective data sheet

1. Product profile

1.1 General description

140 W LDMOS power transistor for Industrial, Scientific and Medical (ISM) applications at frequencies from 2400 MHz to 2500 MHz.

The BLF2425M7L140 and BLF2425M7LS140 are designed for high-power CW applications and are assembled in high performance ceramic packages, available in eared and earless versions

Table 1. Typical performance

Typical RF performance at $T_{case} = 25$ °C in a common source class-AB production test circuit.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	η_{D}
	(MHz)	(V)	(W)	(dB)	(%)
CW	2450	28	140	17.5	52

1.2 Features and benefits

- High efficiency
- High power gain
- Excellent ruggedness
- Excellent thermal stability
- Integrated ESD protection
- Designed for broadband operation (2400 MHz to 2500 MHz)
- Internally matched for ease of use (input and output)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

 Industrial, scientific and medical applications in the frequency range 2400 MHz to 2500 MHz



2. Pinning information

Table 2. Pinning

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Pin	Description		Simplified outline	Graphic symbol
BLF2425M	7L140 (SOT502A)			
1	drain			,
2	gate		- \(\begin{picture}(1) \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\	1
3	source	<u>[1]</u>	2	2 — 3 3 sym112
BLF2425M	7LS140 (SOT502B)			
1	drain			
2	gate		3	ئے
3	source	[1]	2	2 — 3 3 sym112

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

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Type number	Package				
	Name	Description	Version		
BLF2425M7L140	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT502A		
BLF2425M7LS140	-	earless flanged LDMOST ceramic package; 2 leads	SOT502B		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T_{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	225	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 80 ^{\circ}C; P_{L} = 125 W$	0.28	K/W

BLF2425M7L140_2425M7LS140

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6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C unless otherwise specified.

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS} \\$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.16 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 216 \text{ mA}$	1.5	1.8	2.3	V
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	5	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	42	-	Α
I _{GSS}	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	500	nA
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 216 \text{ mA}$	-	1.87	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 7.56 \text{ A}$	-	69	-	mΩ

Table 7. RF characteristics

Test signal: CW; f = 2400 MHz; $V_{DS} = 28$ V; $I_{Dq} = 1300$ mA; $T_{case} = 25$ °C unless otherwise specified in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_p	power gain	P _L = 140 W	15	17.5	-	dB
RLin	input return loss	P _L = 140 W	-	-12	-8	dB
η_{D}	drain efficiency	P _L = 140 W	47	52	-	%

7. Test information

7.1 Ruggedness in class-AB operation

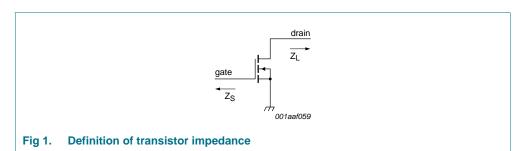
The BLF2425M7L140 and BLF2425M7LS140 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; $I_{Dq} = 1300 \text{ mA}$; $P_{L} = 140 \text{ W}$ (CW); f = 2450 MHz.

7.2 Impedance information

Table 8. Typical impedance

Measured load-pull data. Typical values unless otherwise specified. $I_{Dq} = < tbd>$; $V_{DS} = < tbd>$. Z_S and Z_L defined in Figure 1.

f	Z _S	Z _L
(MHz)	(Ω)	(Ω)
<tbd></tbd>	<tbd></tbd>	<tbd></tbd>



8. Package outline

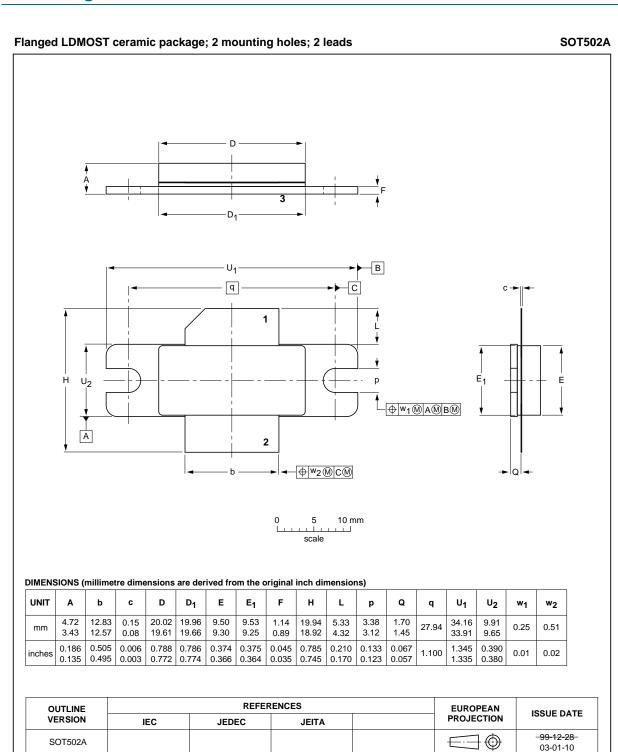


Fig 2. Package outline SOT502A

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Earless flanged LDMOST ceramic package; 2 leads SOT502B U2 2 **→**| **→**| **w**₂ **M**| **D M**| 10 mm scale **DIMENSIONS** (millimetre dimensions are derived from the original inch dimensions) UNIT Ε E₁ Q U_1 U_2 w₂ 19.96 19.94 4.72 12.83 20.02 9.50 9.53 5.33 1.70 20.70 9.91 0.15 1.14 0.25 19.61 3.43 12.57 19.66 9.30 18.92 1.45 0.08 9.25 0.89 4.32 20.45 9.65 0.186 0.505 0.788 0.786 0.374 0.375 0.067 0.006 0.045 0.785 0.210 0.815 0.390 0.010 inches 0.135 0.495 0.003 0.772 | 0.774 | 0.366 | 0.364 0.035 | 0.745 | 0.170 0.057 0.805 0.380

Fig 3. Package outline SOT502B

IEC

OUTLINE

VERSION

SOT502B

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ISSUE DATE

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REFERENCES

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 9. Abbreviations

Acronym	Description
CW	Continuous Wave
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF2425M7L140_2425M7LS140 v.1	20120130	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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BLF2425M7L(S)140

Power LDMOS transistor

14. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
2	Pinning information
3	Ordering information
4	Limiting values
5	Thermal characteristics
6	Characteristics
7	Test information 3
7.1	Ruggedness in class-AB operation 3
7.2	Impedance information
8	Package outline
9	Handling information
10	Abbreviations
11	Revision history
12	Legal information 8
12.1	Data sheet status 8
12.2	Definitions 8
12.3	Disclaimers
12.4	Trademarks S
13	Contact information
14	Contents

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